

Docket: 0756-2330



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

_	Amplication of)
In re Divisional Application of)
Shunpei YAMAZAKI et al.		/
Based On Serial No. 09/352,198 Which Was Filed: July 13, 1999) Art Unit: 2823
) Examiner: B. Kebede
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For:	CRYSTALLINE SEMICONDUCTOR THIN)
101.	FILM, METHOD OF FABRICATING THE)
	SAME, SEMICONDUCTOR DEVICE AND)
	METHOD OF FABRICATING THE SAME) Date: June 29, 2001

INFORMATION DISCLOSURE STATEMENT AND NOTIFICATION OF RELATED APPLICATIONS

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/352,198 filed July 13, 1999.

Copies of some of the references listed on PTO Form-1449 are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The attention of the Examiner is directed to related application Serial No. 09/352,194. A copy the specification is enclosed herewith.

The Examiner's attention is also directed to two articles entitled: Aya et al., "Improvement of SPC poly-Si Film Using the ELA Method", September 11-12, 1997, pp. 167-170, AM-LCD; and Abe et al., High-Performance Poly-Crystalline

Silicon TFT's Fabricated Using the SPC and ELA Methods", July 9-10, 1998, pp. 85-88, AM-LCD.

Respectfully submitted,

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